

# Microelectronics Group

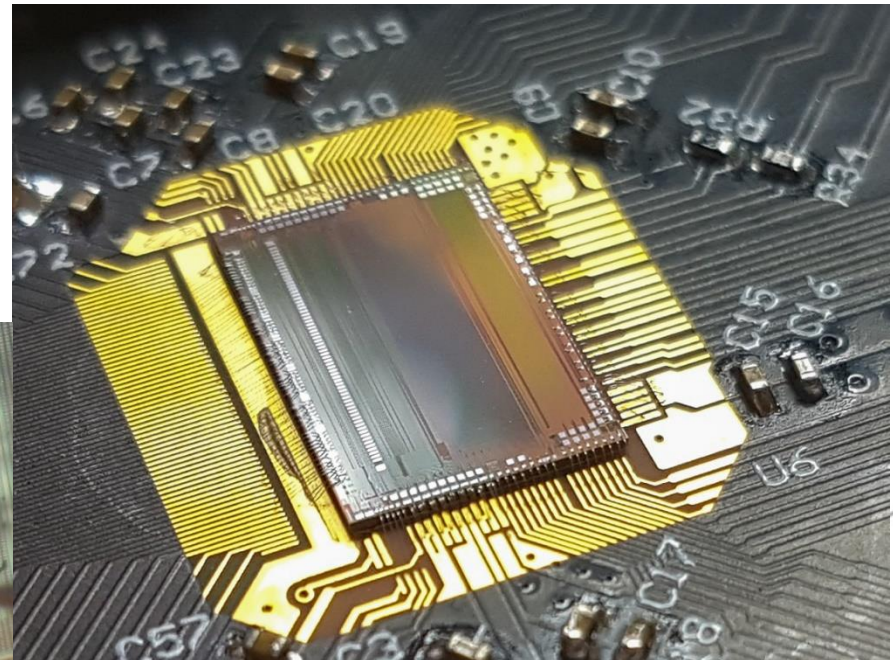
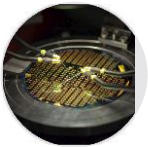
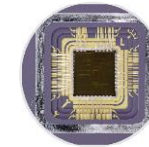
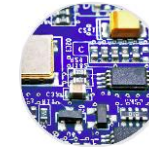
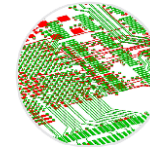
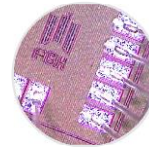
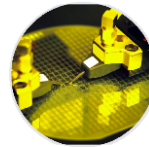
## Dept. Measurement and Electronics

### AGH University of Science and Technology

# Radiation Imaging Systems

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*kasinski@agh.edu.pl*

AKADEMIA GÓRNICZO-HUTNICZA IM. STANISŁAWA STASZICA W KRAKOWIE  
AGH UNIVERSITY OF SCIENCE AND TECHNOLOGY





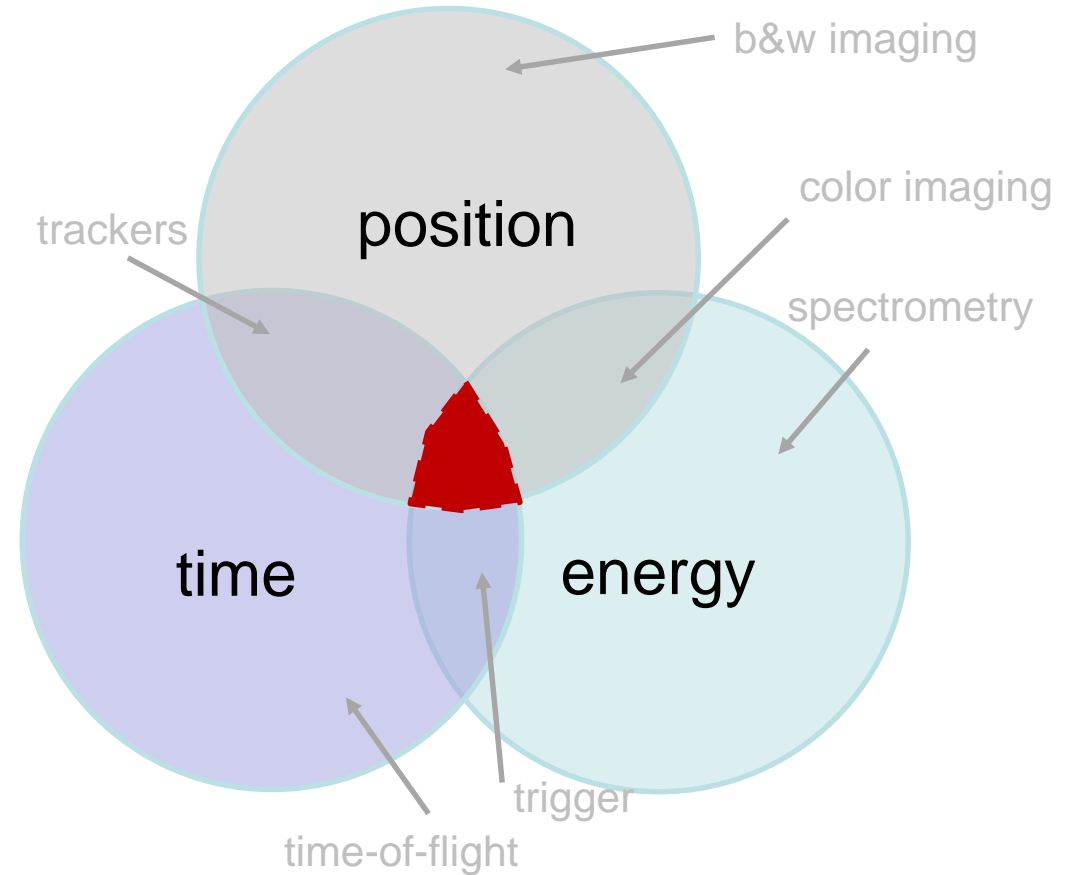
# Our expertise and experience



## *mixed signal (analog and digital) circuits design*

### **Multichannel, integrated circuits design for radiation imaging**

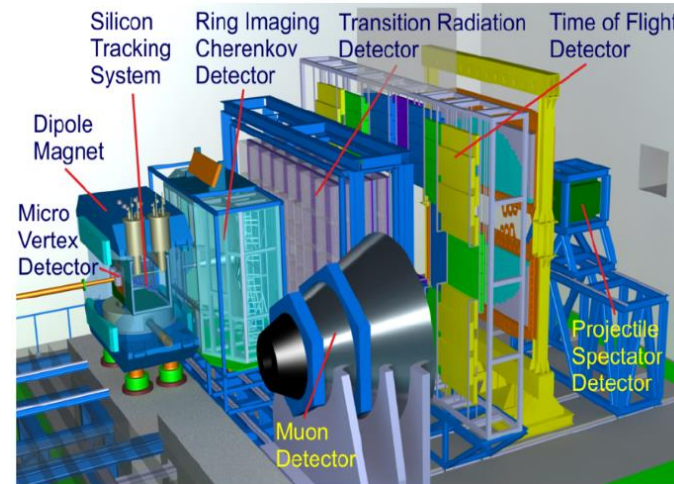
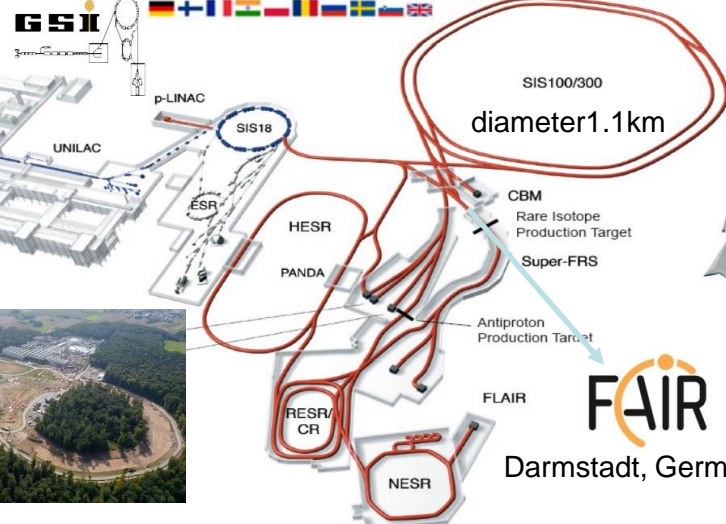
- hybrid pixel detectors, single-photon counting
  - photon counting (energy window)
  - ultra-high speed charge processing & frame-rate
  - low noise and high parameter uniformity
  - charge sharing compensation
- readout circuits for Si microstrip & GEM detectors
  - time and amplitude measurement (ADC in-channel)
  - radiation hardening techniques
- < 40 nm CMOS up to 180 nm CMOS technologies



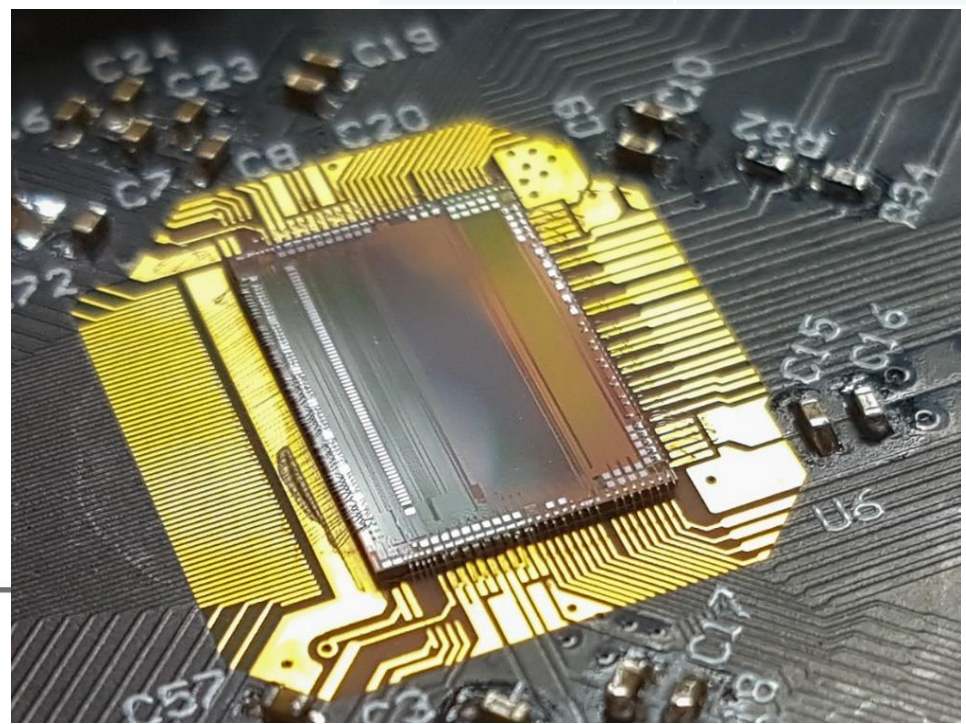
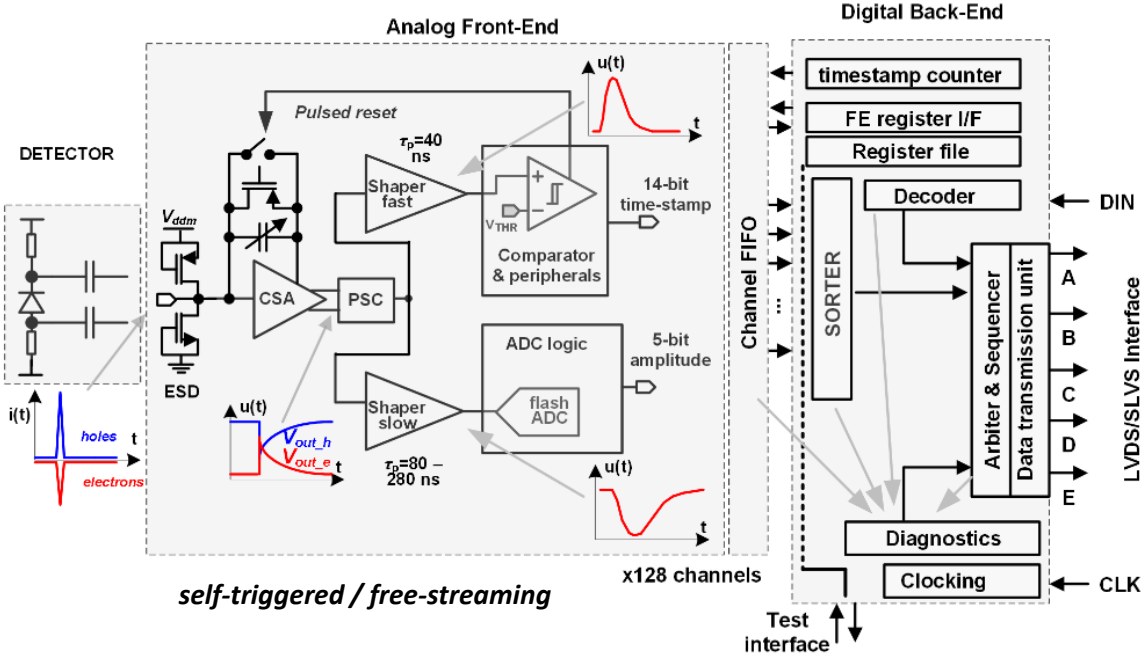


# Amplitude & Time Measurement IC for Silicon Microstrip and GEM detectors at CBM

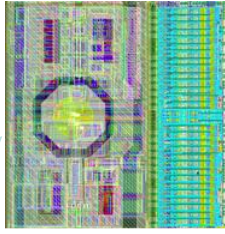
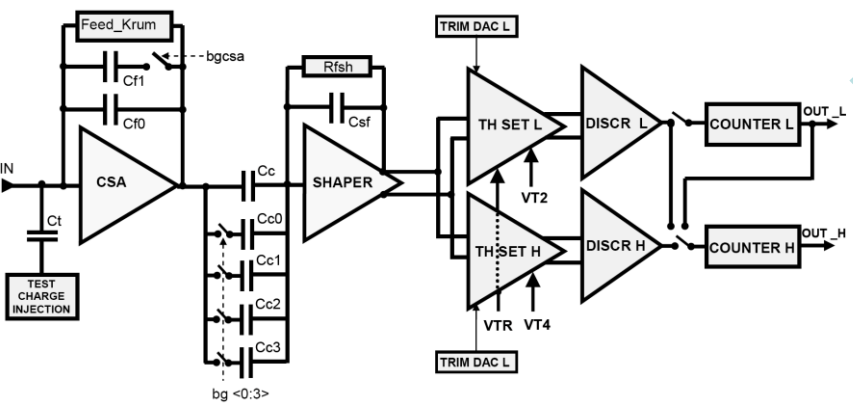
Parameter	Value
<b>Names</b>	STS/MUCH-XYTER2 / SMX2
<b>Process</b>	180 nm CMOS MM/RF
<b>Chip area</b>	10.0 mm × 6.75 mm
<b>Channel number</b>	128 + 2 test
<b>ADC bits</b>	5
<b>Input charge frequency</b>	max. 500 kHz
<b>Power Consumption:</b>	
Uninitialized	0.6 – 1.2 W/chip
Initialized	1.023 W/chip @ $I_d=2$ mA 8 mW/channel
<b>Offset spread of fast channel</b>	1.12 mV rms / 0.015 fC rms (after correction)
<b>Offset spread of ADC [fC]</b>	0.09 (before correction) [39] 0.02 (after correction)
<b>Gain</b>	
Fast shaper (STS)	73 mV/fC
Slow shaper (STS)	32.7 mV/fC
<b>Gain spread:</b>	
Fast shaper	0.8 %
Slow shaper	0.5 % (after calibration)
<b>ENC (Equivalent Noise Charge)</b>	
Fast shaper	44 e <sup>-</sup> /pF + 583 e <sup>-</sup> rms
Slow shaper	27 e <sup>-</sup> /pF + 538 e <sup>-</sup> rms
<b>Slow shaper peaking time [ns]</b>	90 / 180 / 262 / 332



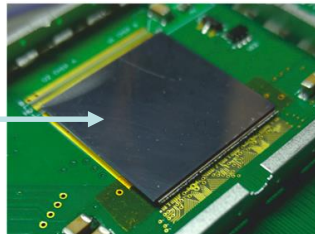
Darmstadt, Germany



# Ultra-Fast X-Ray Imaging Chip for Synchrotron Applications (32 k pixels)

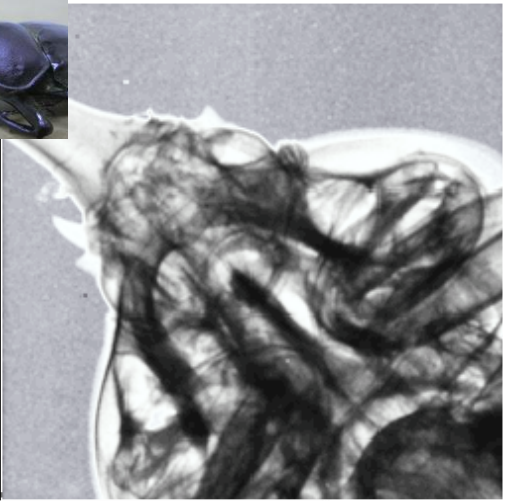
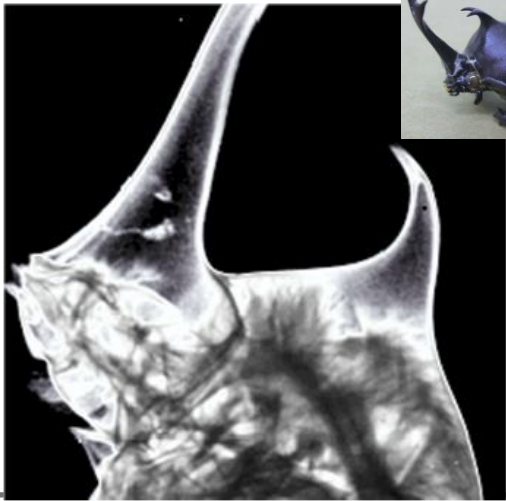
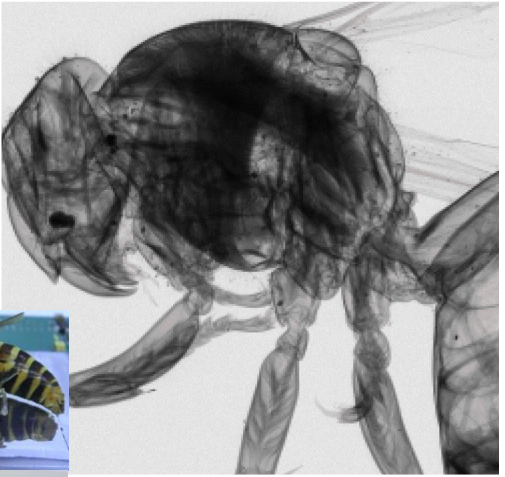
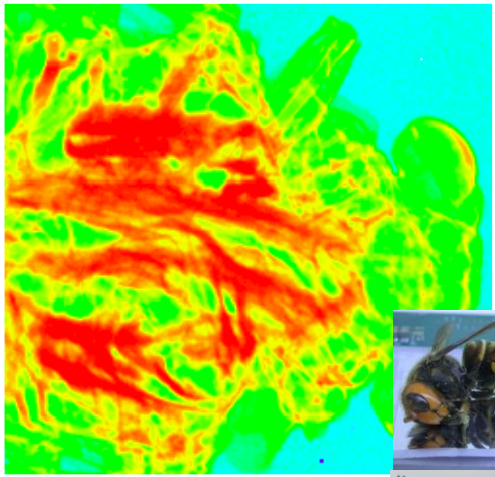


75 x 75  $\mu\text{m}^2$  pixel



## Camera prototype:

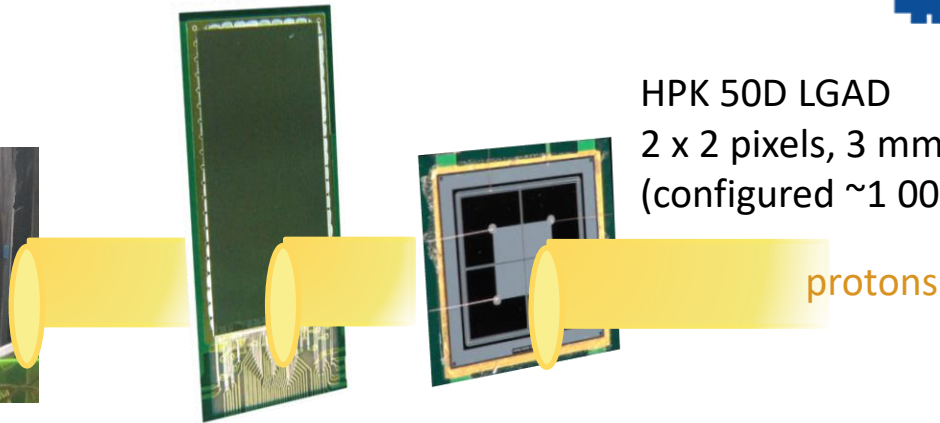
- Built with two UFXC32k IC
- 65536 pixels
- > ~100 Millions of Transistors
- Low noise: 120 electrons rms.
- High data throughput: 3.2 Gbit/s/chip.
- more than 50 000 fps
- Energy-window mode,
- High dynamic range mode,
- Zero dead-time mode
- 3-sides buttable module
- USB, ETH, Camera Link Interfaces



## Testing setup

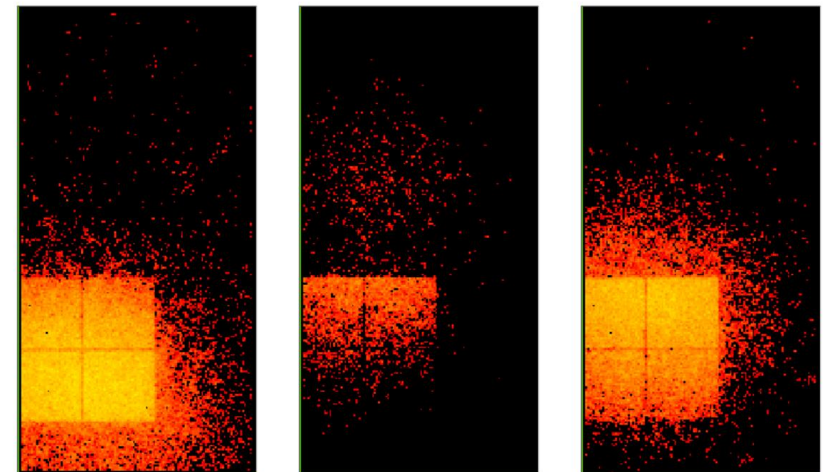
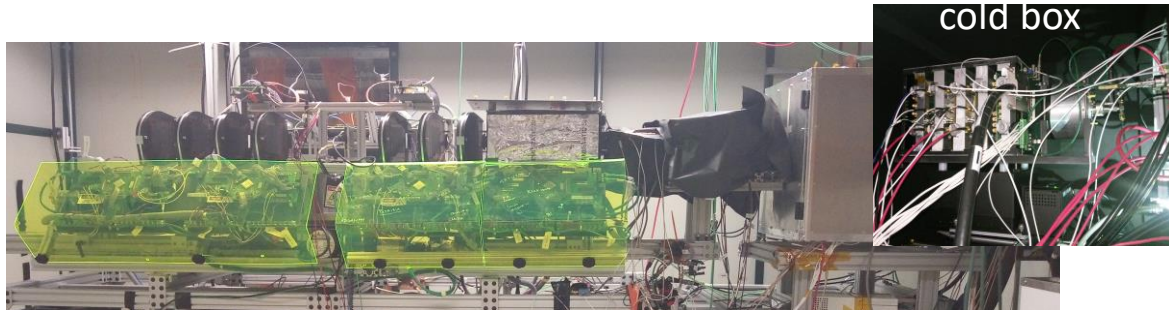


Tracker: FTBF telescope 7 planes of strips  
each 60  $\mu\text{m}$  pitch, 15 deg

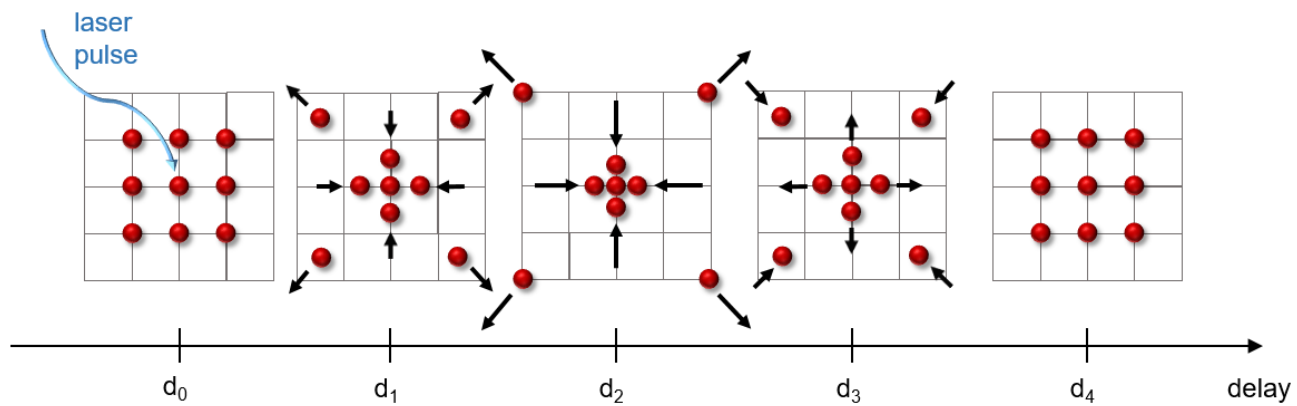
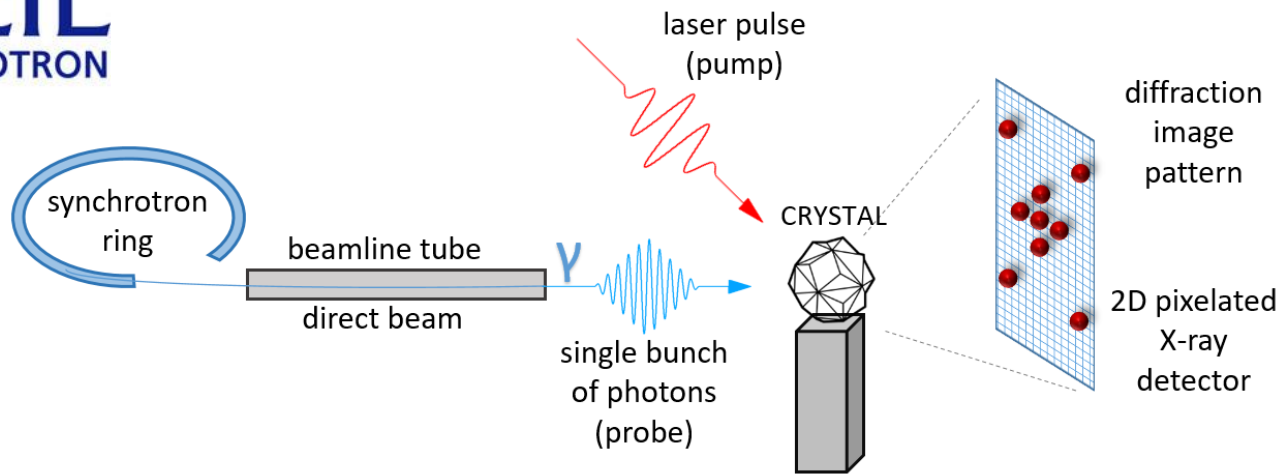


HPK 50D LGAD  
2 x 2 pixels, 3 mm pitch each  
(configured  $\sim 1\,000$  triggers/spill)

UFXC32k SPC HPAD, 128 x 256 pixels,  
75  $\mu\text{m}$  pitch each 320  $\mu\text{m}$  silicon sensor

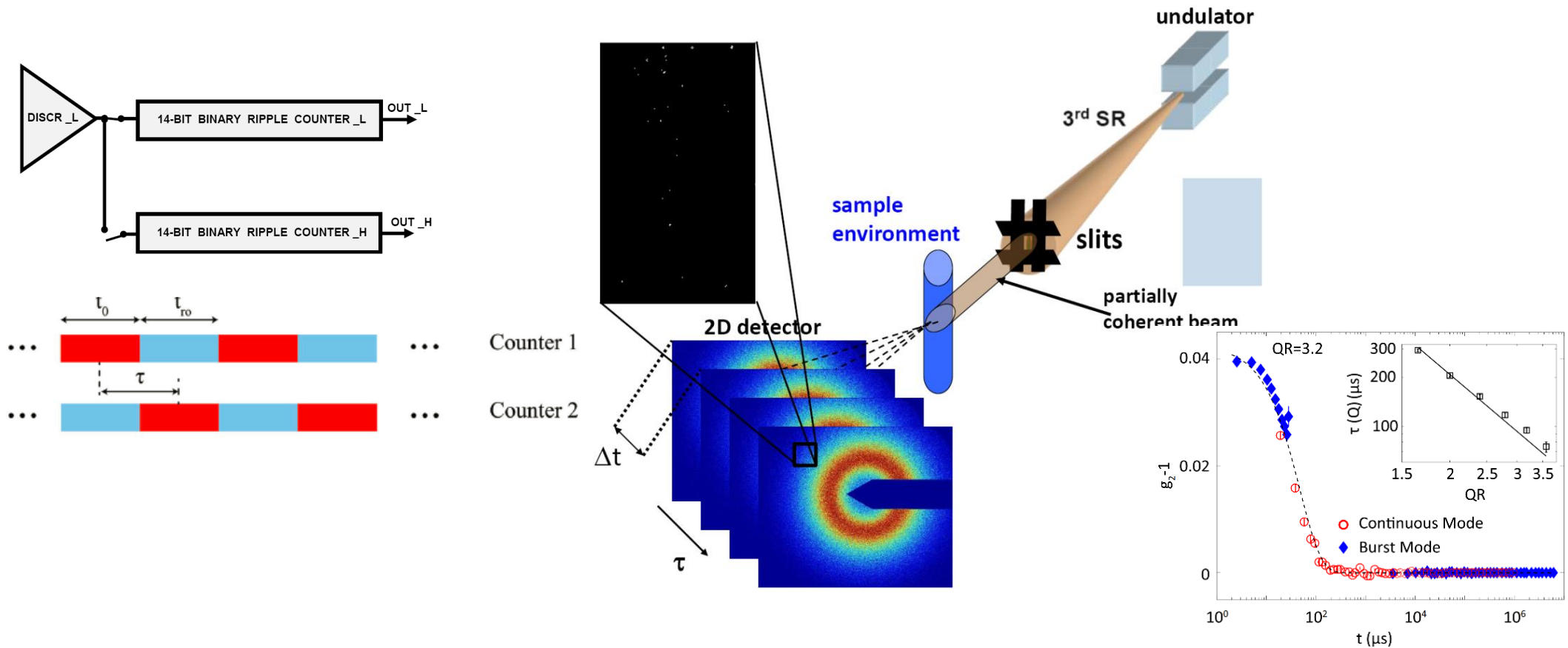


# Tests for pump-probe experiment in SOLEIL



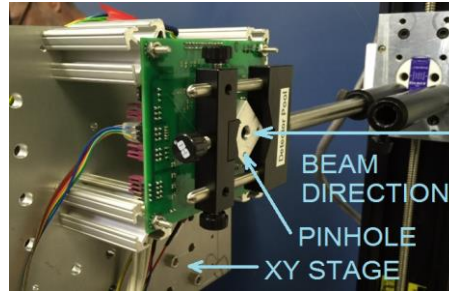
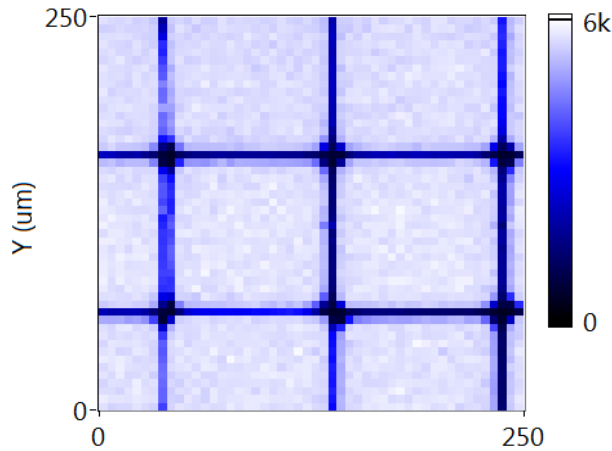
# X-ray Photon Correlation Spectroscopy at Advanced Photon Source in ANL

Unique technique to probe the motion of nanoscale structures over a wide range of length (100 nm – 1 nm) and time scales ( $10^{-6}$  –  $10^3$  seconds) in materials

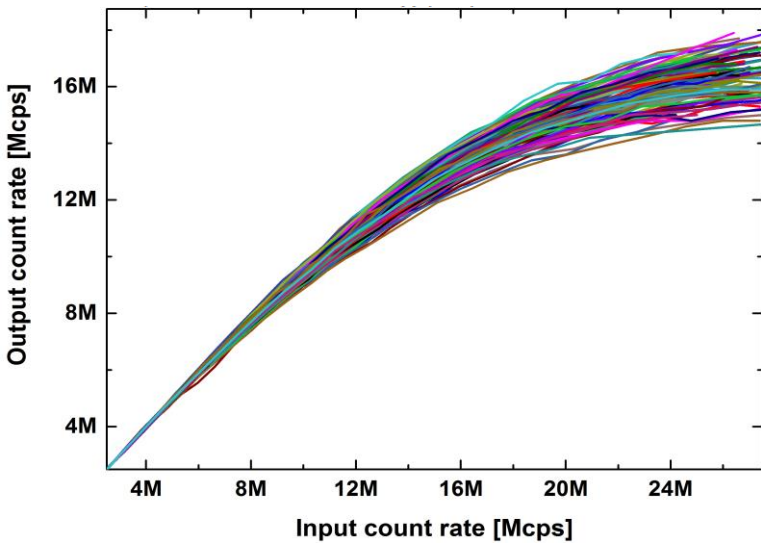
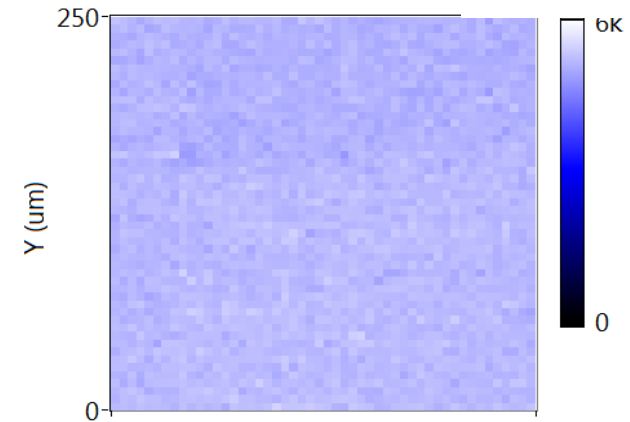


# XY scanning with step 5 $\mu\text{m}$ (pencil beam $\phi = 3.5\mu\text{m}$ ) - ANL

Standard counting



C8P1



Mode	This work	
	FAST_HC	FAST
Process	40 nm	
Pixel size [ $\mu\text{m}^2$ ]	100x100	
Power/pix. [ $\mu\text{W}$ ]	103	46
ENC [ $e^-$ rms]	185	212
10% dead time loss input rate # [cps/pixel]	12 M	12 M
10% dead time loss input rate # [ $\text{photons mm}^{-2} \text{s}^{-1}$ ]	1.2 G	1.2 G

# for count ratio  $N_{OUT}/N_{IN} = 0.9$



## Pixel Readout with Asynchronous Approximation of a Center of Gravity of a Charge Distribution from a Radiation Conversion Event

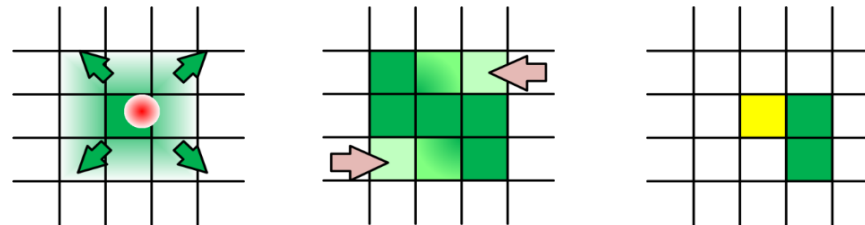
New approach based on pattern recognition. Allocate a hit to a single pixel basing only on the form the area affected by the charge cloud

### Advantages:

- Limited analog processing circuitry (shaper/amplifier, summing node, discriminator).
- Shorter hit processing time.

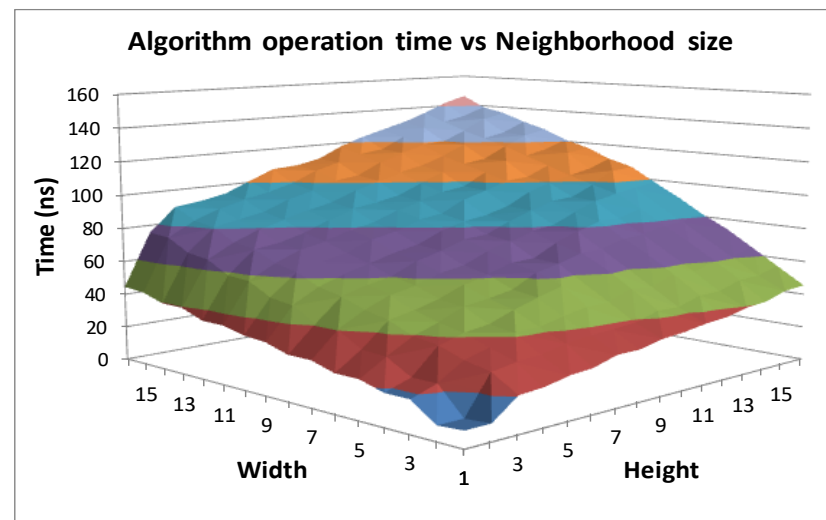
### Challenges:

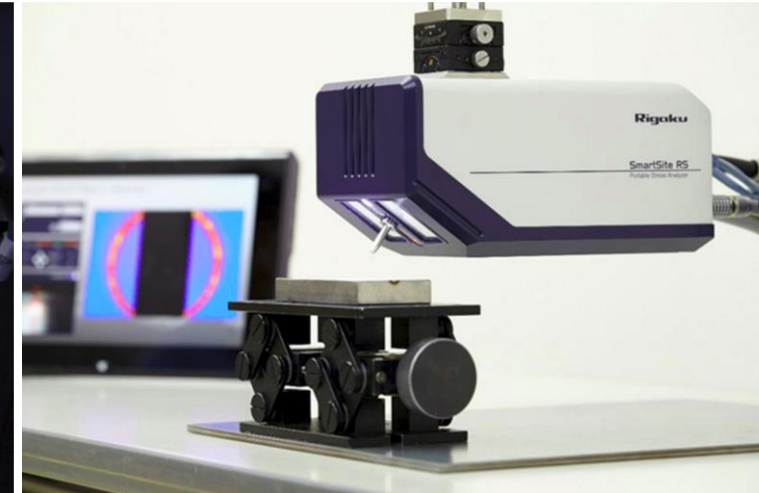
- Dealing with asynchronous nature of the events
- Identification of pixels belonging to the same event.
- Hit allocation algorithm.



Formation phase  $\Rightarrow$  Contraction phase  $\Rightarrow$  Resolution phase

Tested prototype in GF 55nm  
(digital part only)





**D/tex Ultra**, a one-dimensional imaging device which increases the precision of measurement while shortening measurement time.

**Hypix 3000**, a two-dimensional, 16-chip X-ray pixel camera based on the PXD18k ASICs. It belongs to the fastest cameras of this type in the world, and additionally, it is capable of recording photons of precisely determined energy and can operate in a zero dead-time mode.

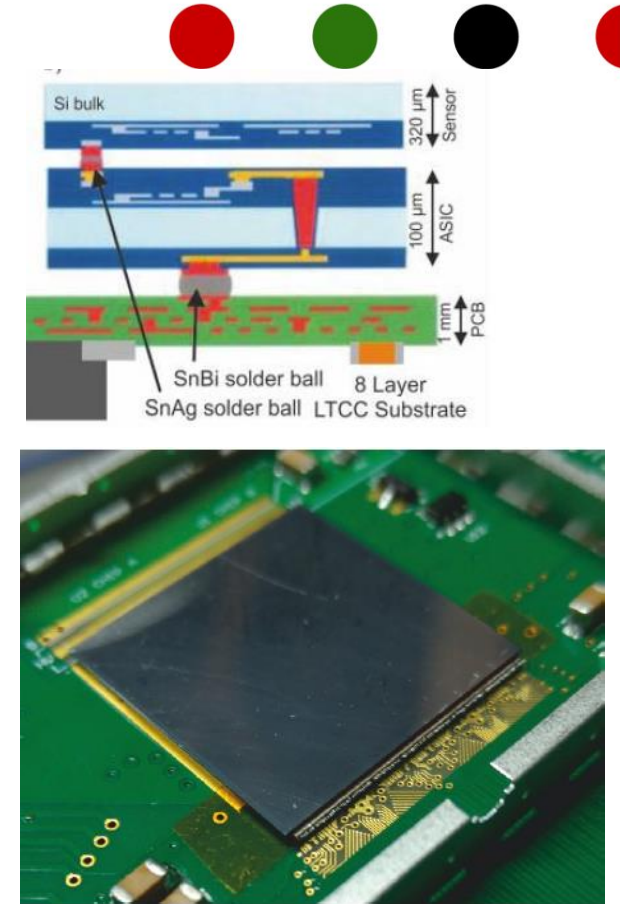
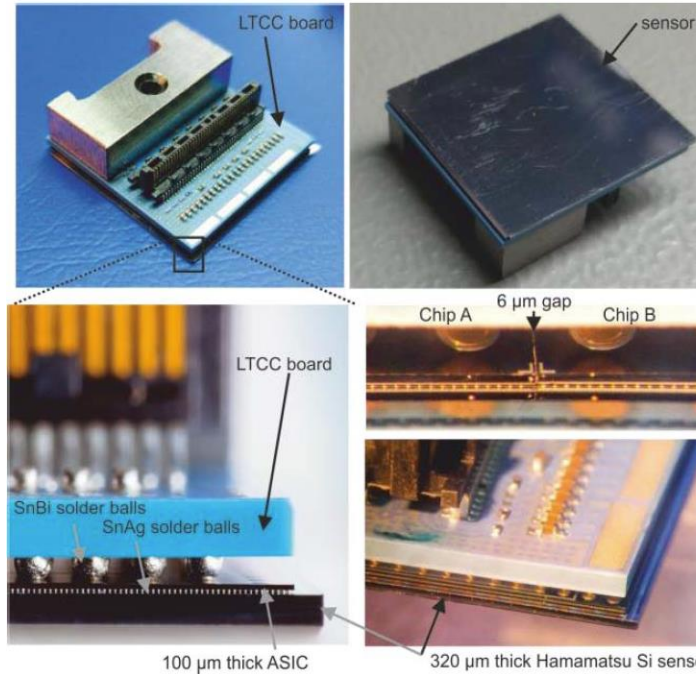
**SmartSite RS**, one of the world's smallest portable analysers of stress in metals (up to 200 mm of inner diameter). It uses the observation of "Debye-Scherrer diffraction rings" of a thin beam of X-rays reflected from the tested element.



# Our expertise and experience

## Radiation imaging microsystems design

- Advanced 3D Microintegration Techniques
  - through-silicon via
  - redistribution layer, flip-chip



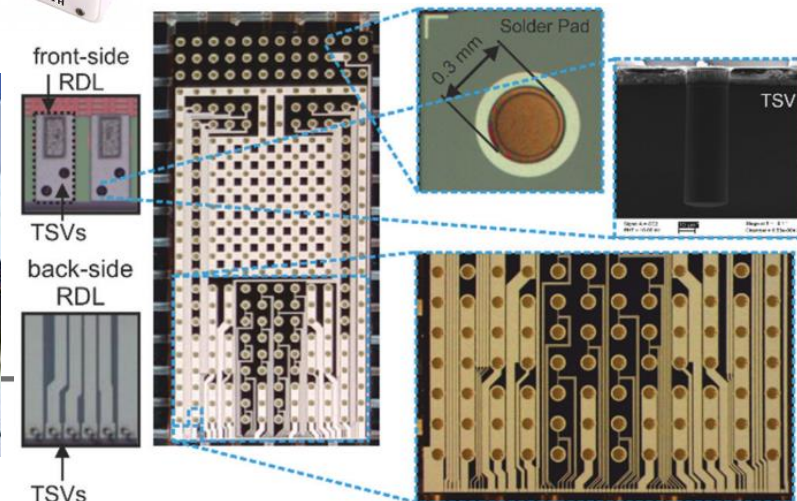
## Printed Circuit Boards design

- mixed-signal: ultra low noise analog & high-speed digital
- signal integrity, power integrity, thermal analyses
- FR4 & ceramic substrates, wire-bonding (in-house)
- wafer probe cards, digital cameras, etc.



## Software Design

- FPGA-based readout (NI PXIe Hardware)
- Automated test software (NI LabVIEW)
- Microcontroller-based systems design





# Cooperation and Network



## X-ray Imaging Hybrid Pixel Detectors

- Fermi National Laboratory, USA
- Argonne National Laboratory, USA
- Synchrotron SOLEIL, France
- Rigaku Corporation, Japan
- KEK, Spring8, Japan
- Fraunhofer IZM Institute for Reliability and Microintegration, Germany
- University College, Ireland
- IMEC, Belgium

## IEEE Solid-State Circuits Society Chapter Poland

- yearly ~5 events, inviting most renowned industrial & academia experts in various fields of microelectronics
- Organization of 2019 45th ESSCIRC/ 49th ESSDERC Cracow, Poland (AGH, WUT, UJ, CEZAMAT)

## Integrated Circuits for HEP Trackers

- GSI Helmholtzzentrum fuer Schwerionenforschung, Germany
- FAIR Center, Germany
- WUT, Warsaw
- Variable-Energy Cyclotron, Kolkata, India
- CBM Collaboration (55 countries)
- CERN
- IMEC, Belgium

Cadence Academic Network  
National Instruments Center of Excellence  
Europractice (Cadence & Mentor)

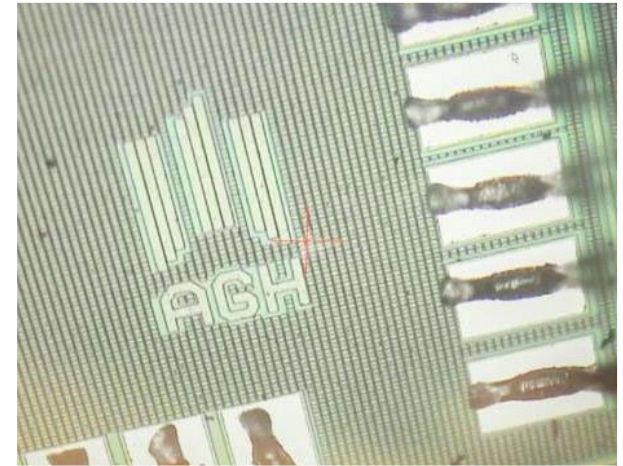


## Microelectronics group

More than 270 scientific papers / patents / books since 2006

More than 55 Integrated Circuits Designs fabricated and tested

More than 24 Research Grants / Industry Projects since 2007



**prof. dr hab inż. Paweł Gryboś**  
**dr hab. inż. Robert Szczygieł, prof. n.**  
dr hab. inż. Grzegorz Deptuch  
dr hab. inż. Marek Miśkiewicz, prof. n.  
dr hab. inż. Piotr Maj, prof. n.  
dr hab. inż. Mirosław Żołędź, prof. n.  
dr hab. inż. Piotr Kmon, prof. n.  
dr inż. Krzysztof Kasiński  
dr inż. Rafał Kłeczek  
dr inż. Piotr Otfinowski  
dr inż. Aleksandra Krzyżanowska  
mgr inż. Anna Kozioł  
mgr inż. Weronika Zubrzycka  
mgr inż. Łukasz Kadłubowski  
mgr inż. Piotr Kaczmarczyk

